

## 2015 M

15 Watts - 28 Volts, Class C Microwave 2000 MHz

The 2015 Class C, utilizes C reliabilit	<b>CRAL DESCRIPTION</b> 5M is a COMMON BASE transistor c: RF output power at 2000 MHz. It incl Gold metalization and diffused ballasti y and supreme ruggedness. The transi ture Solder Sealed package.	CASE OUTLINE 55NV, Style 1	
Maximu	<b>LUTE MAXIMUM RATIN</b> m Power Dissipation @ 25°C <b>m Voltage and Current</b> Collector to Emitter Voltage	NGS 50 Watts 50 Volts	
BVebo	e	3.5 Volts	
Ic	Collector Current	3.0 A	
Maximu	m Temperatures		
Storage Temperature - 65 to +		- 65 to + 200°C	
Operatin	g Junction Temperature	+ 200°C	

## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η <sub>c</sub> VSWR <sub>1</sub>	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 2 GHz Vcb = 28 Volts Po = 15 Watts As Above F = 2 GHz, Po = 15 W	15.0 6.0	7.0 40	3.75 10:1	Watt Watt dB %

BVces BVcbo BVebo Icbo h <sub>FE</sub> Cob θjc	Collector to Emitter Breakdown Collector to Base Breakdown Emitter to Base Breakdown Collector to Base Current Current Gain Output Capacitance Thermal Resistance	Ic = $60 \text{ mA}$ Ic = $6 \text{ mA}$ Ie = $6 \text{ mA}$ Vcb = $28 \text{ Volts}$ Vce = $5 \text{ V}$ , Ic = $600 \text{ mA}$ F = 1 MHz, Vcb = $28 \text{ V}$	50 45 3.5 15	22	3 120 3.5	Volts Volts Wolts mA pF °C/W
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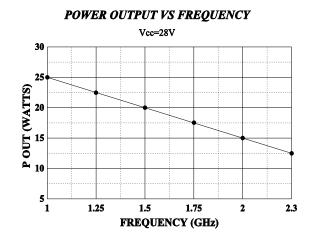
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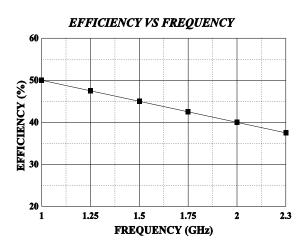
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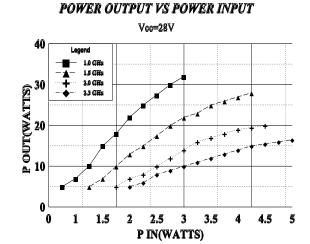
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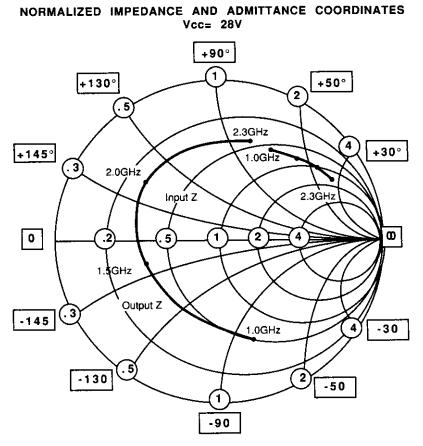




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2015M

## SMITH CHART



NORMALIZED TO A 5 OHM SYSTEM.

